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DBs	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB			
Search Text (oxide\$1 or dioxide\$1) with (BOE or (buffer adj oxide adj etch\$4) or DHF or (dilut\$4 adj HF)) with (SC1 or "SC1" or SC-1 or				
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					USPAT; US-PGPUB;				
	BBC	<u>_</u>	76173	floating adi gate 1	EPO; JPO;	2004/03/04			_
		<u> </u>		noating adj gate#1	DERWENT;	11:08			>
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<u> </u>					USPAT; US-PGPUB;				
	טמ	C	36034	1001001	EPO; JPO;	2004/03/04			
	DK3	77	403/3	controla4 adj gatea i	DERWENT;	11:08	***************************************		>
			-		IBM_TDB				
				STI\$1 or "STI" or	HEDAT. HE DEDITE.				
				(shallow adj trench\$2	EDO: IDO:	70/70/100		••••••••	
	BRS	<u>L3</u>	89839		LIO, JIO, DERWENT	2004/03/04 11:08			0
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	ממת	V <u></u> ⊥	1005	1 cm 2 Cm 2	EPO; JPO;	2004/03/04			
	220	<u> </u>		I allu 2 allu 3	DERWENT;	11:09			>
					IBM_TDB				

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Com or Er Time Stamp ment Defi ro s nitio rs n	2004/03/04 12:00	2004/03/04 11:38	2004/03/04 11:39	2004/03/04 11:40	2004/03/04 12:00
DBs	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	USPAT; US-PGPUB	USPAT; US-PGPUB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
Search Text	(recess\$4 or etch\$4 or clean\$4 or pre-treat\$4 or pre-treat\$5 EPO; JPO; near10 (tunnel\$4 near3 DERWENT; (oxide\$1 or dielectric or IBM_TDB insulat\$4))	4 and 5	("20030124800").PN.	(("20030119256") or ("20020167041")).PN.	(recess\$4) near10 USPAT; US- (tunnel\$4 near3 EPO; JPO; (oxide\$1 or dielectric or DERWENT; insulat\$4)) IBM TDB
Hits	1451	225		2	69
Γ#	LS	F.6	L7	L8	67
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L Number	Hits	Search Text	DB	Time stamp
1	26173	floating adj gate\$1	USPAT;	2004/03/04 11:08
			US-PGPUB,	
			ЕРО; ЈРО;	
}			DERWENT;	
1			IBM TDB	
2	46375	control\$4 adj gate\$1	USPAT;	2004/03/04 11:08
_		,	US-PGPUB;	
1			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
3	89839	STI\$1 or "STI" or (shallow adj trench\$2 adj isolat\$4) or	USPAT;	2004/03/04 11:08
	0,05,	shallow-trench-isolation\$1	US-PGPUB;	200 1103/01 11:00
		bidito w delicit isoladiono i	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
4	1095	(floating adj gate\$1) and (control\$4 adj gate\$1) and (STI\$1 or "STI" or	USPAT;	2004/03/04 11:09
7	1093		1	2004/03/04 11.09
		(shallow adj trench\$2 adj isolat\$4) or shallow-trench-isolation\$1)	US-PGPUB;	
J			EPO; JPO;	
ļ			DERWENT;	
_	1.451		IBM_TDB	2004/02/04 12 00
5	1451	(recess\$4 or etch\$4 or clean\$4 or pre-treat\$4 or pretreat\$5)	USPAT;	2004/03/04 12:00
		near10 (tunnel\$4 near3 (oxide\$1 or dielectric or insulat\$4))	US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	
6	225	((floating adj gate\$1) and (control\$4 adj gate\$1) and (STI\$1 or "STI" or	USPAT;	2004/03/04 11:38
		(shallow adj trench\$2 adj isolat\$4) or shallow-trench-isolation\$1)) and	US-PGPUB;	
		((recess\$4 or etch\$4 or clean\$4 or pre-treat\$4 or pretreat\$4 or treat\$5)	ЕРО; ЛРО;	
		near10 (tunnel\$4 near3 (oxide\$1 or dielectric or insulat\$4)))	DERWENT;	
			IBM_TDB	
7	1	("20030124800").PN.	USPAT;	2004/03/04 11:39
ŀ			US-PGPUB	
8	2	(("20030119256") or ("20020167041")).PN.	USPAT;	2004/03/04 11:40
		, , , , , , , , , , , , , , , , , , , ,	US-PGPUB	
9	69	(recess\$4) near10 (tunnel\$4 near3 (oxide\$1 or dielectric or insulat\$4))	USPAT;	2004/03/04 12:00
			US-PGPUB;	
		·	ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
-	23068	floating adj gate\$1	USPAT;	2004/03/04 11:08
1			US-PGPUB;	
.			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	42151	control\$4 adj gate\$1	USPAT;	2004/03/04 11:08
,	72131	COLLEGIAL GRICAL	US-PGPUB;	2007103104 11.08
			-	
		·	EPO; JPO;	
			DERWENT;	
	14645	(floating adi nata\$1) and (control\$4 = 4: ==4=\$1)	IBM_TDB	2002/04/25 12 22
-	14645	(floating adj gate\$1) and (control\$4 adj gate\$1)	USPAT;	2003/04/25 13:29
l			US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
-	77326	STI\$1 or "STI" or (shallow adj trench\$2 adj isolat\$4) or	USPAT;	2004/03/04 11:08
		shallow-trench-isolation	US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	

-	717	((floating adj gate\$1) and (control\$4 adj gate\$1)) and (STI\$1 or "STI" or	USPAT;	2003/04/25 13:32
		(shallow adj trench\$2 adj isolat\$4) or shallow-trench-isolation)	US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
	ļ		IBM_TDB	
_	33600	CMP or "CMP" or chemical-mechanical-polishing or (chemical adj	USPĀT;	2003/08/10 12:37
		mechanical adj polish\$4)	US-PGPUB;	
		modulation way positive ty	ЕРО; ЛРО;	
			DERWENT;	
			IBM TDB	
	381	(((floating a di gata\$1) and (control\$4 adi gata\$1)) and (CTI\$1 on "CTI"	USPAT;	2003/04/25 13:33
-	381	(((floating adj gate\$1) and (control\$4 adj gate\$1)) and (STI\$1 or "STI"		2003/04/23 13.33
		or (shallow adj trench\$2 adj isolat\$4) or shallow-trench-isolation)) and	US-PGPUB;	
		(CMP or "CMP" or chemical-mechanical-polishing or (chemical adj	ЕРО; ЈРО;	
		mechanical adj polish\$4))	DERWENT;	
			IBM_TDB	
-	24241	floating adj (gate or gates)	USPAT;	2003/08/10 12:35
			US-PGPUB;	
		÷	ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	
<u>-</u>	32533	control adj (gate or gates)	USPAT;	2003/08/10 12:36
	32333	Control and (Europe)	US-PGPUB;	2003/00/10 12:30
			EPO; JPO;	
			DERWENT;	
1				
			IBM_TDB	
-	81667	STI\$1 or "STI" or (shallow adj trench\$2 adj isolat\$4) or	USPAT;	2003/08/10 12:36
		shallow-trench-isolation	US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	
-	37103	CMP or "CMP" or chemical-mechanical-polishing or (chemical adj	USPAT;	2003/08/10 12:37
	İ	mechanical adj polish\$4)	US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
l _	15204	(floating adj (gate or gates)) and (control adj (gate or gates))	USPAT;	2003/08/10 12:38
-	13204	(Houring adj (gate of gates)) and (control adj (gate of gates))	US-PGPUB;	2005/00/10 12.50
	j		ЕРО; ЛРО;	
			DERWENT;	
	455	(0 4: 1:4 4) 14 4 1 1:4 4 1 (07701	IBM_TDB	2002/00/10 12 20
-	455	(floating adj (gate or gates)) and (control adj (gate or gates)) and (STI\$1	USPAT;	2003/08/10 12:38
		or "STI" or (shallow adj trench\$2 adj isolat\$4) or	US-PGPUB;	
1		shallow-trench-isolation) and (CMP or "CMP" or	ЕРО; ЛРО;	
		chemical-mechanical-polishing or (chemical adj mechanical adj	DERWENT;	
i		polish\$4))	IBM_TDB	
-	24266	protru\$8 with (trench\$2 or dielectric\$1 or insulat\$5 or oxide)	USPAT;	2003/08/10 12:40
			US-PGPUB;	
	į		ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	
-	67	((floating adj (gate or gates)) and (control adj (gate or gates)) and	USPAT;	2003/08/10 12:59
		(STI\$1 or "STI" or (shallow adj trench\$2 adj isolat\$4) or	US-PGPUB;	
		shallow-trench-isolation) and (CMP or "CMP" or	ЕРО; ЛРО;	
		chemical-mechanical-polishing or (chemical adj mechanical adj	DERWENT;	
		polish\$4))) and (protru\$8 with (trench\$2 or dielectric\$1 or insulat\$5 or		•
		•	IBM_TDB	
		oxide))	LIGDAT	2002/00/10 12 21
-	22	trench\$2 with (corner\$1 or edge\$1) with round\$4 with (hydrogen or H2	USPAT;	2003/08/10 13:04
		or "H2" or "H.sub.2")	US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	

-	84	trench\$2 with (hydrogen or H2 or "H2" or "H.sub.2") with anneal\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/10 13:07
-	1	(trench\$2 with (hydrogen or H2 or "H2" or "H.sub.2") with anneal\$4) and (((floating adj (gate or gates)) and (control adj (gate or gates)) and (STI\$1 or "STI" or (shallow adj trench\$2 adj isolat\$4) or shallow-trench-isolation) and (CMP or "CMP" or chemical-mechanical-polishing or (chemical adj mechanical adj polish\$4))) and (protru\$8 with (trench\$2 or dielectric\$1 or insulat\$5 or oxide)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/10 13:05
-	2195	(wet near4 (oxidi\$8 or oxida\$8)) with oxide\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/10 13:08
-	17	(N2 or "N2" or "N.sub.2") with ((wet near4 (oxidi\$8 or oxida\$8)) with oxide\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/10 13:09
-	91	(poly\$1 or polysilicon or (polycrystal\$8 adj silicon)) with (LPCVD or LP-CVD or (low adj pressure adj chemical adj vapor adj deposit\$5) or ((LP or (low adj pressure)) adj (CVD or (chemical adj vapor adj deposit\$5)))) with (silane or disilane or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or "Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6") with (Ph3 or "Ph3" or "Ph.sub.3" or "P H.sub.3")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/10 14:42
-	3149	((silicon adj nitride) or Si3N4 or "Si3N4" or "Si.sub.3N.sub.4" or "Si.sub.3 N.sub.4") with (H3PO4 or "H3PO4" or "H.sub.3PO.sub.4" or "H.sub.3 PO.sub.4" or "H.sub.3 PO.sub.4" or (phosphoric adj acid\$1) or phosphoricacid\$1 or phosphoric-acid\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/10 14:43
-	201	(poly\$1 or polysilicon or (polycrystal\$8 adj silicon)) with (LPCVD or LP-CVD or (low adj pressure adj chemical adj vapor adj deposit\$5) or ((LP or (low adj pressure)) adj (CVD or (chemical adj vapor adj deposit\$5)))) with (silane\$1 or disilane\$1 or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6") with (Ph3 or "Ph3" or "Ph.sub.3" or "P H.sub.3" or phosphine\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/10 14:44
-	47	(((silicon adj nitride) or Si3N4 or "Si3N4" or "Si.sub.3N.sub.4" or "Si.sub.3 N.sub.4") with (H3PO4 or "H3PO4" or "H.sub.3PO.sub.4" or "H.sub.3 PO.sub.4" or "H.sub.3 PO.sub.4" or (phosphoric adj acid\$1) or phosphoricacid\$1 or phosphoric-acid\$1)) and ((poly\$1 or polysilicon or (polycrystal\$8 adj silicon)) with (LPCVD or LP-CVD or (low adj pressure adj chemical adj vapor adj deposit\$5) or ((LP or (low adj pressure)) adj (CVD or (chemical adj vapor adj deposit\$5)))) with (silane\$1 or disilane\$1 or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6") with (Ph3 or "Ph3" or "Ph.sub.3" or "P H.sub.3"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/10 14:45
-	0	or phosphine\$1)) ((((silicon adj nitride) or Si3N4 or "Si3N4" or "Si.sub.3N.sub.4" or "Si.sub.3 N.sub.4") with (H3PO4 or "H3PO4" or "H.sub.3PO.sub.4" or "H.sub.3 PO.sub.4" or "H.sub.3 PO.sub.4" or "H.sub.3PO.sub.4" or (phosphoric adj acid\$1) or phosphoricacid\$1 or phosphoric-acid\$1)) and ((poly\$1 or polysilicon or (polycrystal\$8 adj silicon)) with (LPCVD or LP-CVD or (low adj pressure adj chemical adj vapor adj deposit\$5) or ((LP or (low adj pressure)) adj (CVD or (chemical adj vapor adj deposit\$5)))) with (silane\$1 or disilane\$1 or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6") with (Ph3 or "Ph3" or "Ph.sub.3" or "P H.sub.3" or phosphine\$1))) and (trench\$2 with (hydrogen or H2 or "H2" or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/10 14:45

-	2	((((silicon adj nitride) or Si3N4 or "Si3N4" or "Si.sub.3N.sub.4" or	USPAT;	2003/08/10 14:45
1		"Si.sub.3 N.sub.4") with (H3PO4 or "H3PO4" or "H.sub.3PO.sub.4" or	US-PGPUB;	
		"H.sub.3 P O.sub.4" or "H.sub.3 PO.sub.4" or "H.sub.3P O.sub.4" or	ЕРО; ЛРО;	
		(phosphoric adj acid\$1) or phosphoricacid\$1 or phosphoric-acid\$1)) and	DERWENT;	
		((poly\$1 or polysilicon or (polycrystal\$8 adj silicon)) with (LPCVD or	IBM_TDB	
		LP-CVD or (low adj pressure adj chemical adj vapor adj deposit\$5) or		
		((LP or (low adj pressure)) adj (CVD or (chemical adj vapor adj		
		deposit\$5)))) with (silane\$1 or disilane\$1 or SiH4 or "SiH4" or		
		"SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6"		
		or "Si.sub.2 H.sub.6") with (Ph3 or "Ph3" or "Ph.sub.3" or "P H.sub.3"		
		or phosphine\$1))) and (floating adj (gate or gates)) and (control adj		
		(gate or gates))		